RoHS

COMPLIANT HALOGEN

FREE

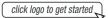


Vishay Semiconductors

Hyperfast Rectifier, 2 A FRED Pt®



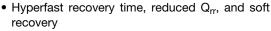
DESIGN SUPPORT TOOLS

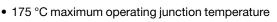




PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 A			
V_{R}	100 V			
V _F at I _F	0.72 V			
t _{rr}	25 ns			
T _J max.	175 °C			
Package	SlimSMA (DO-221AC)			
Circuit configuration	Single			

FEATURES





- Low forward voltage drop
- · Low leakage current
- Specific for output and snubber operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		100	V	
Average rectified forward current	I _{F(AV)}	T _C = 155 °C ⁽¹⁾	2	۸	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	65	Α	
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

Note

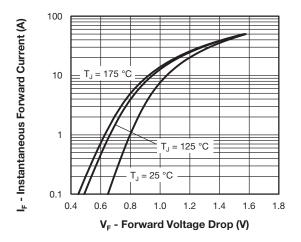
⁽¹⁾ Device on PCB with 8 mm x 16 mm soldering lands

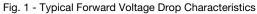
ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	100	-	-	.,
Forward voltage	V _F	I _F = 2 A	-	0.85	0.93	V
Forward voltage		I _F = 2 A, T _J = 125 °C	-	0.72	0.77	
Reverse leakage current I _R		$V_R = V_R$ rated	-	-	2	μA
	'R	T _J = 125 °C, V _R = V _R rated	-	0.5	8	μΑ
Junction capacitance	C _T	V _R = 100 V	-	10	-	pF



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	25	ı	20
Reverse recovery time t _{rr}	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25		
	T _J = 25 °C		-	17	-	ns	
	T _J = 125 °C	$I_F = 2 A$ $dI_F/dt = 200 A/\mu s$ $V_R = 160 V$	-	24	-		
Peak recovery current I _{RRM}	T _J = 25 °C		-	2	-	Α	
	T _J = 125 °C		-	3	-	A	
Reverse recovery charge Q		T _J = 25 °C		-	17	-	nC
	Q_{rr} $T_J = 125 ^{\circ}C$	T _J = 125 °C		-	37	-	

THERMAL - MECHANICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	12	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	115	C/VV
Approximate weight				0.03		g
Approximate weight				0.0011		OZ.
Marking device		Case style SlimSMA (DO-221AC)		21	H2	





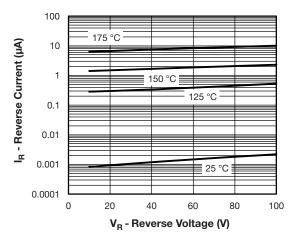


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

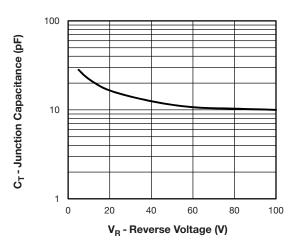


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

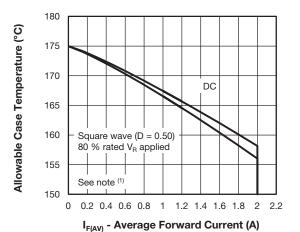


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

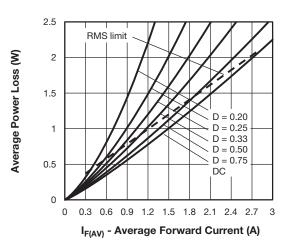


Fig. 5 - Forward Power Loss Characteristics

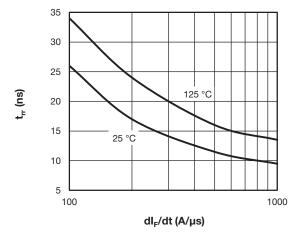


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

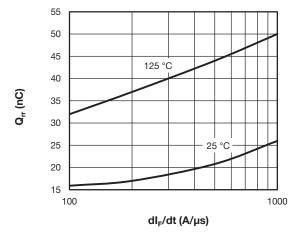
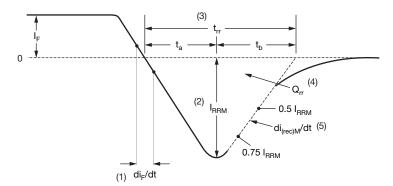


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see Fig. 6); $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = rated V_R$

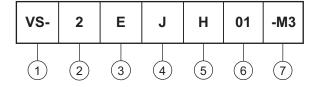


- (1) di_F/dt rate of change of current through zero crossing
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (5) di_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- Current rating (2 = 2 A)
- 3 Circuit configuration:

E = single diode

J = SlimSMA package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (01 = 100 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

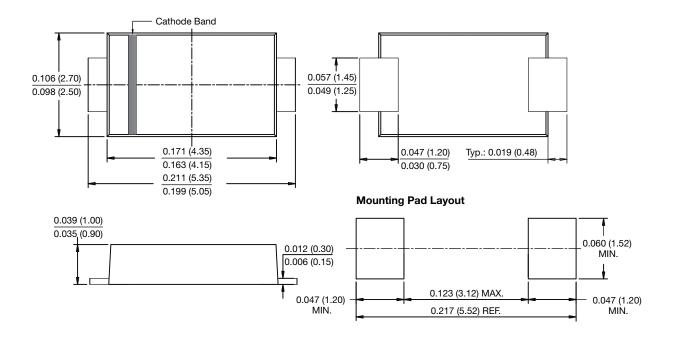
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-2EJH01-M3/6A	3500	3500	7"diameter plastic tape and reel		
VS-2EJH01-M3/6B	14 000	14 000	13"diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95771			
Part marking information	www.vishay.com/doc?95562			
Packaging information	www.vishay.com/doc?88869			



DO-221AC (SlimSMA)

DIMENSIONS in inches (millimeters)





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Vishay

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